

Technical Data Data Sheet N1201, Rev. - Green Products

240NQ020-1 SCHOTTKY RECTIFIER

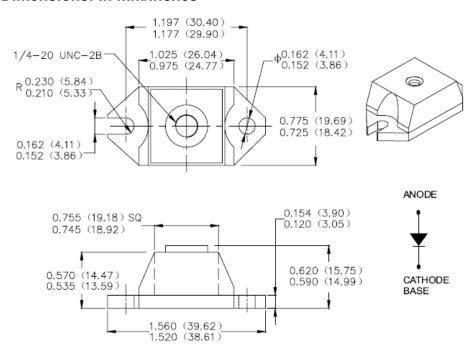
Applications:

- Parallel switching power supply Free-Wheeling diodes Reverse battery protection
- Redundant power subsystems

Features:

- 125 [°]C T_J operation(V_R<5V)
- Unique high power, Half-Pak module
- Optimized for OR-ing applications
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Ultra low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/Inches



PRM1-1(HALF PAK Module)

MARKING, MOLDING RESIN

Marking for 240NQ020-1, 1st row SS YYWWL, 2nd row 240NQ020-1 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin Epoxy resin UL:94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	20	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =70°C, rectangular wave form	240	А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	3600	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 240A, Pulse, T _J = 25 °C	0.48	V
	V_{F2}	@ 240A, Pulse, T _J = 125 °C	0.35	V
Max. Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	24	mA
leg) *	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	2600	mA
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	16000	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	5.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

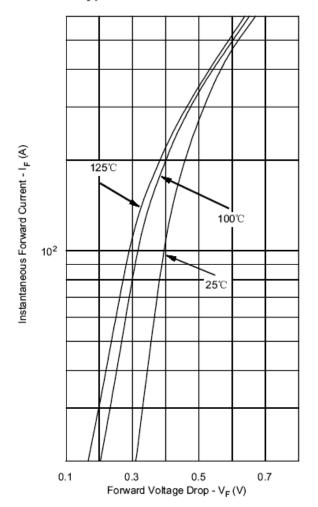
Characteristics	Symbol	Condition	Specifi	Units		
Max. Junction Temperature	T_J	-	-55 to +125		°C	
Max. Storage Temperature	T _{stg}	-	-55 to +150		°C	
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.20		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W	
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm	
Approximate Weight	wt	-	25.6		g	
Case Style	PRM1-1					

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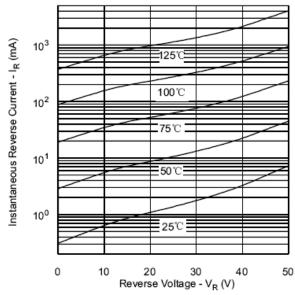


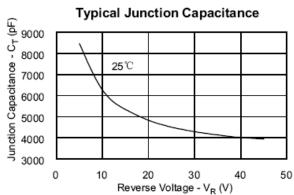
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Typical Forward Characteristics



Typical Reverse Characteristics





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